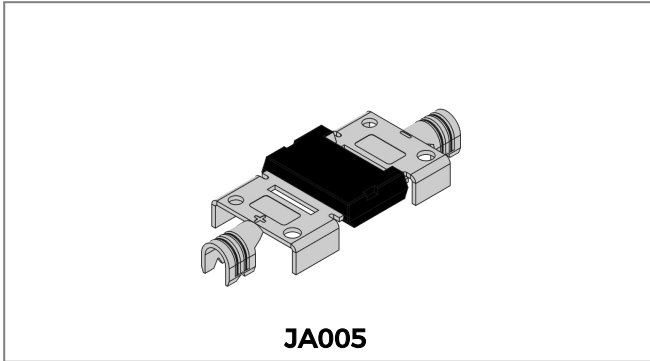


GFJ4145TS Power Schottky Module Bypass Diode



Features

- Trench MOS Schottky technology
- Low thermal resistance
- Lower forward voltage drop, low power loss
- Isolate Package design, ideal for heat dispersion
- High forward current capability
- Excellent anti-humidity
- Low profile package
- High forward surge capability
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Mechanical Data

- Case: JA005
- High temperature soldering guaranteed
- Heated-tool welding 260°C, 10 seconds
- Marking Code: GFJ4145TS

Maximum Ratings (limiting values, at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	45	V
Average Rectified Forward Current	$I_{F(AV)}$	$T_C = 119^\circ\text{C}$, In DC	40	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse	350	A
Rating for fusing ($t < 8.3\text{ms}$)	I^2t	$T_J = 25^\circ\text{C}$	750	A ² sec

Electrical Characteristics

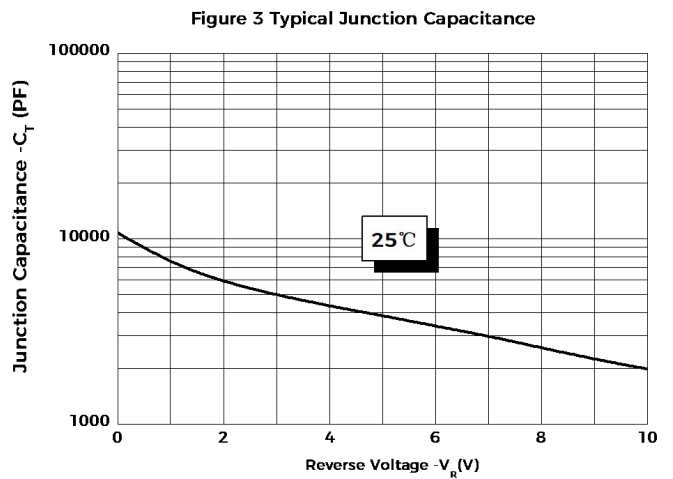
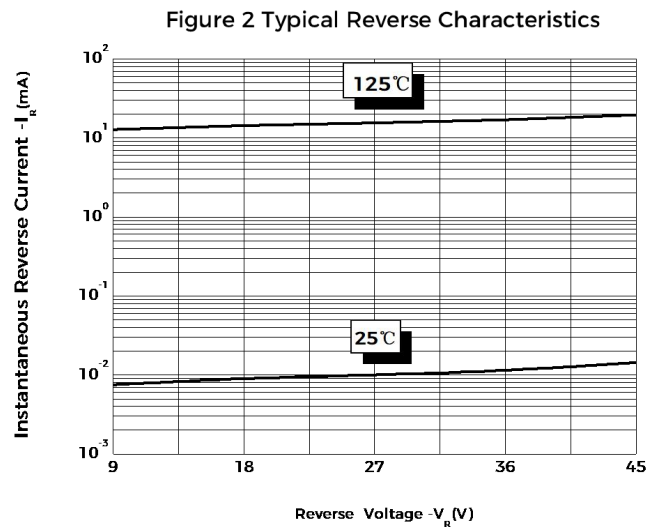
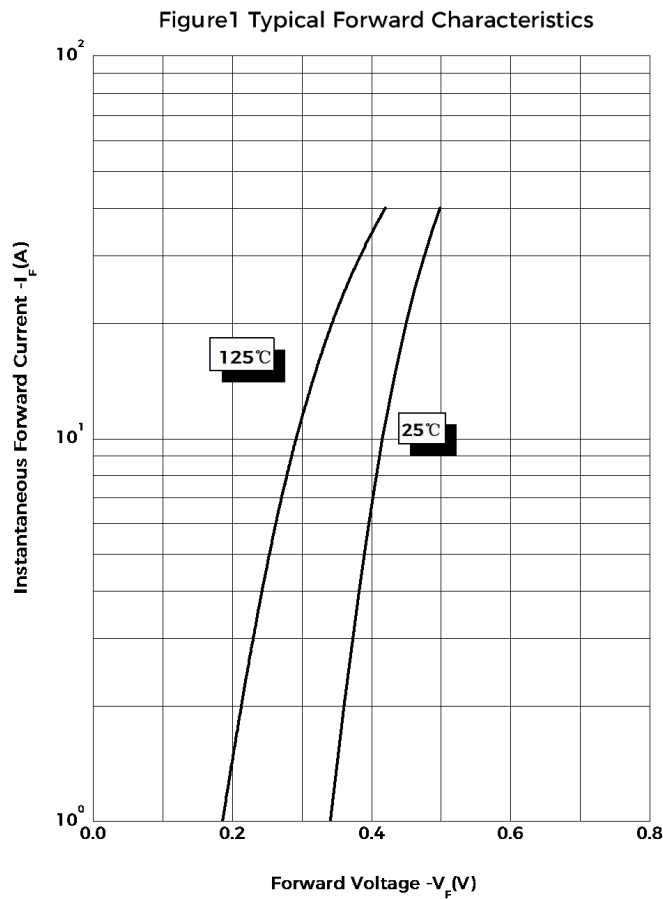
Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 40A, Pulse, $T_J = 25^\circ\text{C}$	0.50	0.52	V
Reverse Current*	I_{R1}	@ $V_R = \text{rated } V_R$, $T_J = 25^\circ\text{C}$	0.01	0.20	mA
	I_{R2}	@ $V_R = \text{rated } V_R$, $T_J = 100^\circ\text{C}$	-	20	mA
	I_{R3}	@ $V_R = \text{rated } V_R$, $T_J = 125^\circ\text{C}$	19	55	mA
Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	3831	-	pF

* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications(Ta=25°C Unless otherwise specified)

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	IN DC Forward Mode, without reverse bias, $t \leq 1$ h	-55 to +200	°C
Storage Temperature	T_{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	-	1.0	°C/W

Ratings and Characteristics Curves

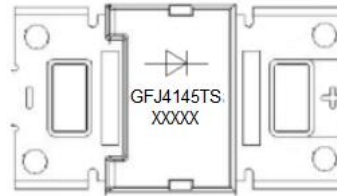


Technical Data
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Ordering Information

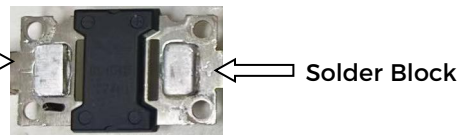
Device	Package	Shipping
GFJ4145TS	JA005	30pcs/Tube

Marking Diagram



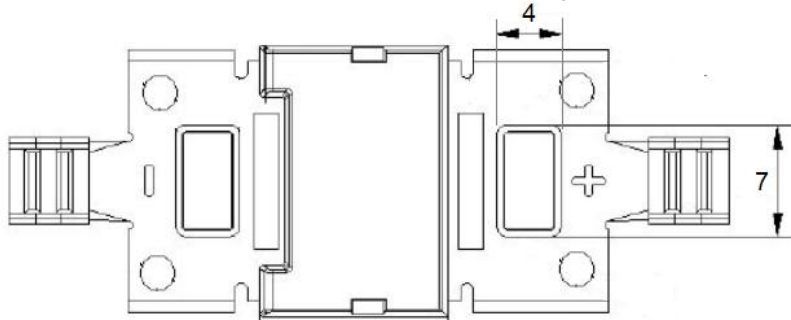
Where XXXXX is YYWWL
 GFJ4145TS = Device Code
 YY = Year
 WW = Week
 L = Lot Number

Order P/N	Terminals	Additional
GFJ4145TS-S1	Tin Plated	None
GFJ4145TS-S3	Tin Plated	Solder Block

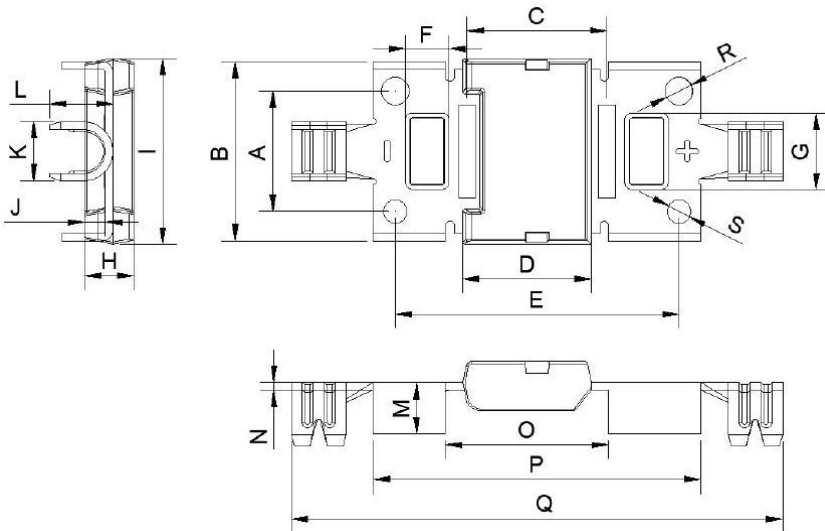


Solder block Specification

The composition of the tin block is Sn50Pb50 with flux.
 The size of the tin block is $6(\pm 0.15) \times 3.5(\pm 0.15) \times 1(\pm 0.08)$ mm.
 The composition and size of tin blocks can be customized according to customer requirements.
 Solder block to be centered, not exceed the flat groove.



Mechanical Dimensions JA005 (Millimeters)



Symbol	Dimensions in millimeters	
	Min.	Max
A	10.5	11.5
B	15.9	16.9
C	12.6	13
D	11.23	12.23
E	25.5	26.5
F	3.5	4.5
G	6.5	7.5
H	4.3	4.7
I	16.5	17.5
J	1.7	2.1
K	5	5.8
L	5.6	6
M	4.4	5
N	0.6	0.8
O	14.73	15.13
P	29.5	30.5
Q	44.5	45.5
R	2.35	2.65
S	2	2.3

Technical Data

Data Sheet N3073 REV.-

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